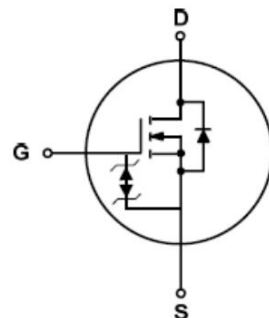
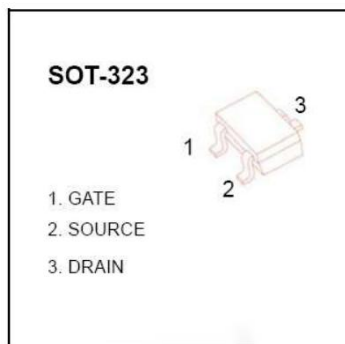


N-Channel MOSFET

$BV_{DSS}, T_A=25^{\circ}\text{C}$	$I_D, T_A=25^{\circ}\text{C}$	$R_{DS(on), \text{max}} @ 4\text{V}$
30V	0.1A	8Ω

Features

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel
- ESD Protect



Marking:KN

Absolute Maximum Ratings($T_C=25^{\circ}\text{C}$, unless otherwise noted.)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	30	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	0.1	A
Maximum Power Dissipation	P_D	0.2	W
Operating Junction Temperature Range	T_J	-55~150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55~150	$^{\circ}\text{C}$

Thermal Characteristics

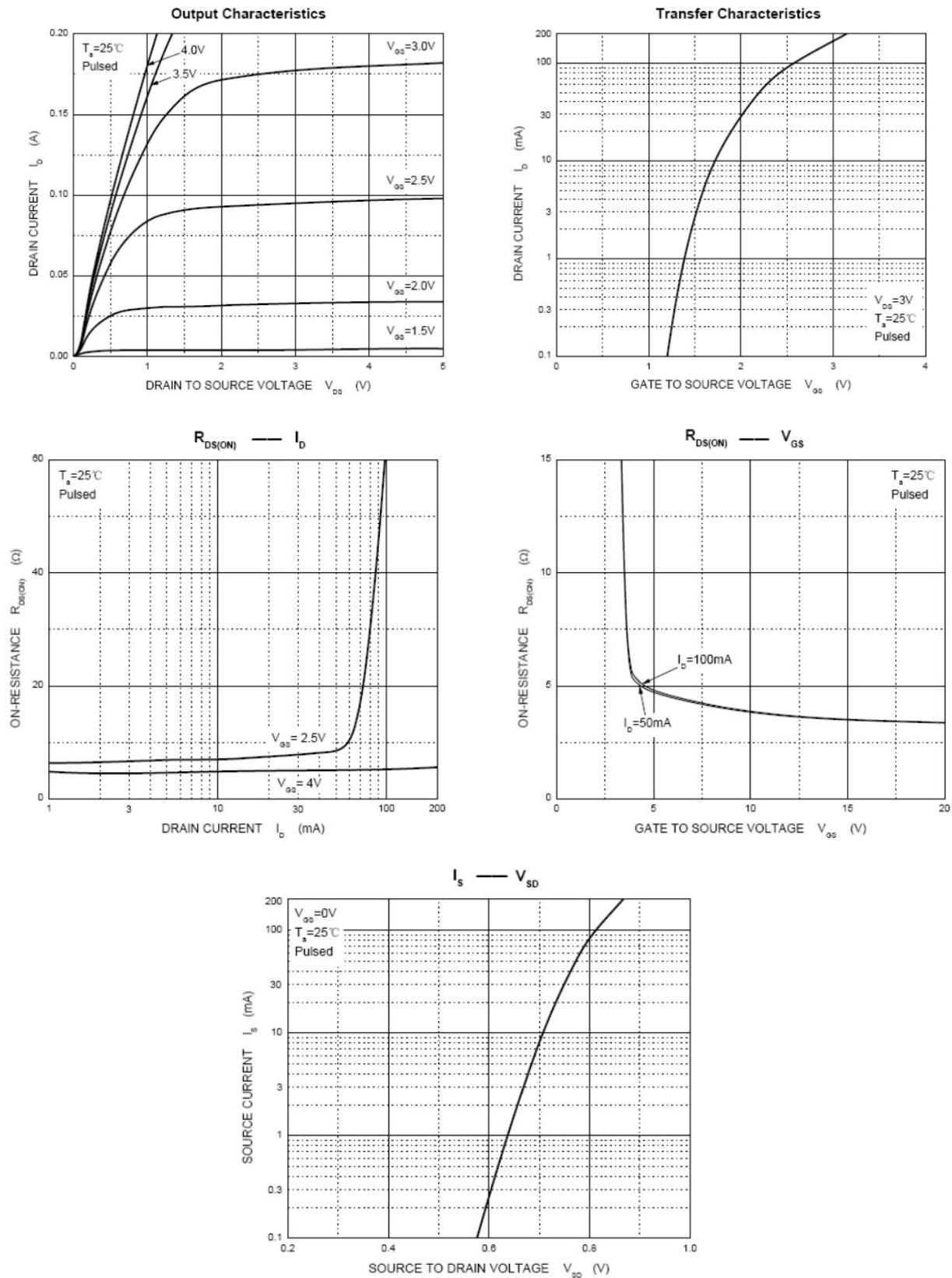
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to ambient, Max.	$R_{\theta JA}$	625	$^{\circ}\text{C/W}$

Electrical Characteristics($T_A=25^{\circ}\text{C}$, unless otherwise noted.)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source Breakdown voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=10\mu\text{A}$	30			V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			0.2	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=+20\text{V}, V_{DS}=0\text{V},$			+10	μA
		$V_{GS}=-20\text{V}, V_{DS}=0\text{V},$			-10	μA
Gate Threshold voltage	$V_{GS(th)}$	$V_{DS}=3\text{V}, I_D=100\mu\text{A}$	0.8		1.5	V
Static Drain to Source on resistance	$R_{DS(on)}$	$V_{GS}=4\text{V}, I_D=10\text{mA}$			8	Ω
		$V_{GS}=2.5\text{V}, I_D=1\text{mA}$			13	Ω
Forward transconductance	g_{fs}	$V_{DS}=3\text{V}, I_D=10\text{mA}$	20			mS

Dynamic Characteristics						
Input Capacitance	Ciss	V _{DS} =5V,V _{GS} =0V, f=1MHz		13		pF
Output Capacitance	Coss			9		pF
Reverse Capacitance	Crss			4		pF
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{DD} =5V,V _{GS} =5V,I _D =10mA, R _G =10Ω,R _L =500Ω		15		nS
Turn-On Rise Time	t _r			35		nS
Turn-Off Delay Time	t _{d(off)}			80		nS
Turn-Off Fall Time	t _f			80		nS
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _D =100mA			1.1	V

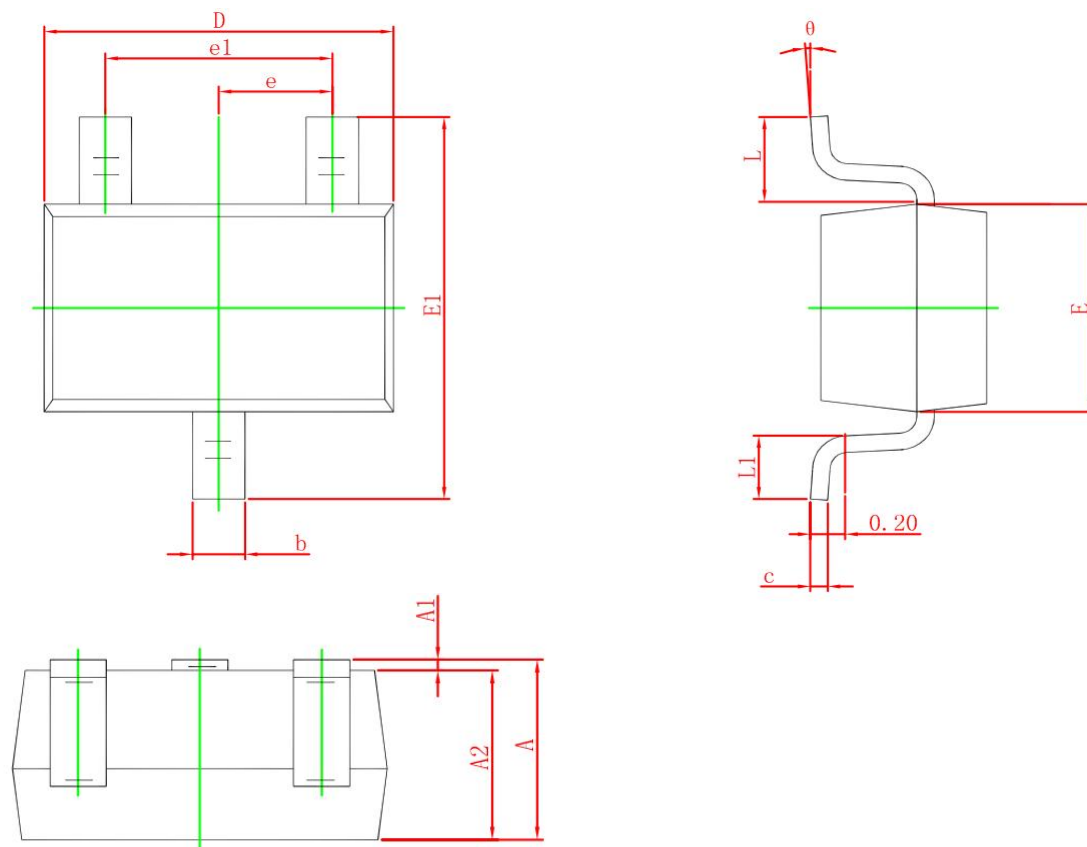
Typical Characteristics



Package Information

SOT-323

Dimensions in mm



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°